



# United States Patent and Trademark Office



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231 www.uspto.gov

APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/803,624 03/09/2001		Yoshikazu Kojima	81738.0292	7882		
26021	7590	01/31/2002				
HOGAN &			EXAMINER			
500 S. GRA SUITE 1900			FENTY, JESSE A			
LOS ANGELES, CA 90071-2611				ART UNIT	PAPER NUMBER	
				2815	2815 DATE MAILED: 01/31/2002	
				DATE MAILED: 01/31/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.



		P	
Application No.	Applicant(s)		
09/803,624	KOJIMA ET AL.		
Examiner	Art Unit		

		09/803,624	KOJIMA ET AL.						
	Office Action Summary	Examiner	Art Unit						
		Jesse A Fenty	2815						
	- The MAILING DATE of this communication app	ears on the cover sheet with the o	correspondence address						
Period for Reply  A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  It the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).									
1)[🖂	Status 1)⊠ Responsive to communication(s) filed on <u>09 March 2001</u> .								
2a)[☐	, and the second	s action is non-final.							
3)	Since this application is in condition for allowa closed in accordance with the practice under <i>E</i>								
Disposition of Claims									
4) 🖂	Claim(s) 26-28 is/are pending in the applicatio	n.							
4	a) Of the above claim(s) is/are withdraw	vn from consideration.							
5)	5) Claim(s) is/are allowed.								
6)⊠	6)⊠ Claim(s) <u>26-28</u> is/are rejected.								
7)	Claim(s) is/are objected to.								
8)	Claim(s) are subject to restriction and/or	election requirement.							
Application	on Papers								
9) <u> </u>	he specification is objected to by the Examiner	•							
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.									
	Applicant may not request that any objection to the	e drawing(s) be held in abeyance. S	ee 37 CFR 1.85(a).						
11) 🗌 T	he proposed drawing correction filed on	is: a) ☐ approved b) ☐ disappro	oved by the Examiner.						
If approved, corrected drawings are required in reply to this Office action.									
12) 🔲 T	The oath or declaration is objected to by the Exa	aminer.							
	nder 35 U.S.C. §§ 119 and 120								
13)	Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a	a)-(d) or (f).						
a)[	☐ All b) ☐ Some * c) ☐ None of:								
	1. Certified copies of the priority documents	s have been received.							
	<ol><li>Certified copies of the priority documents</li></ol>	s have been received in Applicat	ion No						
<ul> <li>Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>									
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).									
a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.									
Attachment(s)									
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) <u>2</u>	5) Notice of Informal	y (PTO-413) Paper No(s) Patent Application (PTO-152)						

Application/Control Number: 09/803,624

Art Unit: 2815

#### **DETAILED ACTION**

## Claim Rejections - 35 USC § 112

- The following is a quotation of the second paragraph of 35 U.S.C. 112:
  - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claims 26-28 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
  - a. In re claim 26, the terms "high-drain-withstand-voltage MOSFET" and "low-drain-withstan-voltage MOSFET" are vague and indefinite in that the terms do not distinguish a particular structure that one skilled in the art would readily identify.

## Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claim 26, as best understood, is rejected under 35 U.S.C. 102(b) as being anticipated by Haken (U.S. Patent No. 5,024,960).

In re claim 26, Haken (Figs. 1-6) discloses a semiconductor device, comprising:

An HVMISFET formed on a semiconductor region and having a gate insulating film of a thickness in the range of 100-200 angstroms (column 2, line 23);

Application/Control Number: 09/803,624

Art Unit: 2815

An LVMISFET of the same conductivity type on the substrate, having the same thickness gate insulating film; and

Drain and source regions being constituted of phosphorus impurity regions.

The limitation, "a surface ... being partially increased to make ... 0.7V" is a recitation of the intended use of the claimed device. Terms that simply set forth the intended use, a property inherent in or a function, do not differentiate the claimed composition of these elements from those known to prior art.

### Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claim 27 is rejected under 35 U.S.C. 103(a) as being unpatentable over Haken (as above).

In re claim 27, Haken discloses the device of claim 26, but does not expressly disclose the gate length in the range of 1.5 to 2.5 microns. However, it would have been obvious to one having ordinary skill in the art at the time the invention was made to determine the optimum gate length based on the thinness of the gate oxide layer, since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. *In re Boesch*, 617 F. 2c 272, 205 USPQ 215 (CCPA 1980).

Application/Control Number: 09/803,624

Art Unit: 2815

### Allowable Subject Matter

5. Claim 28, additionally specifying the HVMISFET comprising a source and drain comprising low and high concentration regions surrounding a channel-forming region, and a field insulating film with a thickness at least one order of ten greater than that of the gate insulating film formed above the low-concentration drain region, would be allowable if rewritten to overcome the rejection(s) under 35 U.S.C. 112, second paragraph, set forth in this Office action and to include all of the limitations of the base claim and any intervening claims.

#### Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Nozaki (U.S. Patent No. 5,847,432); Iwai et al. (U.S. Patent No. 5,276,346); and Ando et al. (U.S. Patent No. 5,285,096) disclose similar semiconductor structures, each comprising some variation of the claimed invention.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jesse A Fenty whose telephone number is 703-308-8137. The examiner can normally be reached on 5/4-9 1st Fri. Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on 703-308-1690. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-746-3892 for After Final communications.



Art Unit: 2815

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Jesse A Fenty Examiner Art Unit 2815

Jan**y**ary 28, 2002

EDDIE LEE

SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800